

Product Overview

NSS1C201L: 100 V, 2.0 A NPN Low $V_{CE(sat)}$ Bipolar Transistor

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- These Devices are PbFree, Halogen Free/BFR Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

Benefits

- No Lead

Applications

- Power management

End Products

- Portable and battery powered products

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}^{Max}$ (V)	I_C Cont. (A)	V_{CEO}^{Min} (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(0)}$ (V)	h_{FE}^{Min}	h_{FE}^{Max}	f_T^{Min} (MHz)	P_{TM}^{Max} (W)	Package Type
NSS1C201LT1G	0.11	Pb-free Halide free non AEC-Q and PPAP	Active	NPN	Low $V_{CE(sat)}$	0.09	2	100	140	7	0.95	0.85	120	360	-	0.71	SOT-23-3
NSV1C201LT1G	0.1645	AEC Qualified PPAP Capable Pb-free Halide free	Active	NPN	Low $V_{CE(sat)}$	0.09	2	100	140	7	0.95	0.85	120	360	-	0.71	SOT-23-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 4/16/2021